

SLOVENSKI STANDARD SIST EN 150014:2002

01-september-2002

Blank detail specification: Thyristor-diodes, transient overvoltage suppressor

Blank Detail Specification: Thyristor-diodes, transient overvoltage suppressor

Vordruck für Bauartspezifikation: Thyristor-Dioden, Überspannungs-Begrenzer

Spécification particulière cadre: Diodes-thyristor, limiteurs de surtensions transitoires

Ta slovenski standard je istoveten z: EN 150014:1996

<u>SIST EN 150014:2002</u>

https://standards.iteh.ai/catalog/standards/sist/6f064b0f-c8d4-4809-bdc0-25fa587a3039/sist-en-150014-2002

ICS:

31.080.10 Diode Diodes 31.080.20 Tiristorji Thyristors

SIST EN 150014:2002 en

SIST EN 150014:2002

iTeh STANDARD PREVIEW (standards.iteh.ai)

SIST EN 150014:2002

https://standards.iteh.ai/catalog/standards/sist/6f064b0f-c8d4-4809-bdc0-25fa587a3039/sist-en-150014-2002

EUROPEAN STANDARD NORME EUROPÉENNE EUROPÄISCHE NORM

EN 150014

February 1996

ICS 31.080.10

Supersedes CECC 50014:1994

Descriptors: Quality, blank detail specification, thyristor diode

English version

Blank Detail Specification: Thyristor diodes, transient overvoltage suppressor

Spécification particulière cadre: Diodes-thyristor, limiteurs de surtensions transitoires Vordruck für Bauartspezifikation: Thyristor-Dioden, Überspannungs-Begrenzer

iTeh STANDARD PREVIEW

This European Standard was approved by CENELEC on 1995-09-20. CENELEC members are bound to comply with the CEN/CENELEC Internal Regulations which stipulate the conditions for giving this European Standard the status of a national standard without any alteration 9-bdc0-

Up-to-date lists and bibliographical references concerning such national standards may be obtained on application to the Central Secretariat or to any CENELEC member.

This European Standard exists in three official versions (English, French, German). A version in any other language made by translation under the responsibility of a CENELEC member into its own language and notified to the Central Secretariat has the same status as the official versions.

CENELEC members are the national electrotechnical committees of Austria, Belgium, Denmark, Finland, France, Germany, Greece, Iceland, Ireland, Italy, Luxembourg, Netherlands, Norway, Portugal, Spain, Sweden, Switzerland and United Kingdom.

CENELEC

European Committee for Electrotechnical Standardization Comité Européen de Normalisation Electrotechnique Europäisches Komitee für Elektrotechnische Normung

Central Secretariat: rue de Stassart 35, B-1050 Brussels

Foreword Contents					
At the request of Working Group CLC/TC CECC/WG 5, the text of CECC 50014:1994, Issue 1, was submitted to the formal vote for conversion into a European Standard. It was approved by CENELEC as EN 150014 on 1995-09-020 The following date was fixed: — latest date by which the EN has to be implemented at national level by publication of an identical national standard or by endorsement: (dop) 1996-09-01	Foreword 1 Mechanical description 2 Short description 3 Quality assessment level(s) 4 Limiting values 5 Electrical characteristics 6 Marking 7 Ordering information 8 Test conditions and inspection				
endorsement (dop) 1996-09-01 Preface This specification was prepared by CECC WG 5	requirements 9 Additional information Annex A Typical waveforms 10				
It is based, wherever possible, on the publications of the International Electrotechnical Commission.	Annex B Measurements methods 1: Annex C Electrical endurance 1:				
The text of this specification was circulated to the CECC for voting in the document indicated below and was ratified by the President of the CECC for printing as a CECC Specification. (Standard)	DARD PREVIEW ards.iteh.ai)				
(Secretariat) http(Secretariat).ai/catalog/	EN 150014:2002 standards/sist/6f064b0f-c8d4-4809-bdc0- 39/sist-en-150014-2002				

2 © BSI 02-2000

	THYRISTOR DIODE	TRAN	SIENT S	SUPPRESS	SOR		
	ess) of responsible ONH [1] Page CECC 50014-xxx [CECC detail specification number plus issue number and/or date]						
ELECTRONIC COMPONENT OF ASSESSED [3] QUALITY IN ACCORDANCE WITH: CECC 50000, issue [and national references if different] [National number of detail specification This box may not be used if National number includes CECC number]						n [4]	
1 Mechanical description Either outline references (code A), or base and case references (codes B and D) — according to IEC 191-2 — national (if desired) OUTLINE DRAWING AND CONNECTIONS [7] DETAIL SPECIFICATION FOR: [Type number(s) of relevant device(s) and, if appropriate, structurally similar devices] ORDERING INFORMATION See 7 of this specification							
(terminal connected to case, if any) [Characteristics of the optical port of the device, defined with regard to its mechanical axis] MARKING [See 2.5 of CECC 50000 and/or 6 of this specification] 2 Short description Construction Semiconductor material: Case material: Transient overvoltage protection, etc. 3 Quality assessment level(s) [8]							e
	DENTIFICATION SIST EN 150 CECC/50000 lis. iteh. ai/catalog/standar		WZ =	e n from A nr 8d4-4809-bdc		CECC 50	0000]
4 Limiting values (Absolute maximum rating system IEC 134) [9]						[9]	
	over the operating temperature r hat a value shall be inserted in th				ed.		
Paragraph CECC 50014	[Repeat only clause numbers used, with text. Additional values, if any, shall be given at the appropriate place without clause number(s) Curves should preferably be given in 9 of this specification.]		Symbol	Va min.	lue max.	Unit	
4.1	Minimum and maximum operation case temperature	ng aml	oient or	$egin{array}{c} T_{ m amb} \ T_{ m case} \end{array}$	X X	X X	°C °C
4.2	Minimum and maximum storage Maximum soldering temperature conditions	-		$egin{array}{c} \mathbf{T_{stg}} \\ \mathbf{T_{sld}} \end{array}$	X	X	°C
Information a in the current	oout manufacturers who have com CECC 00200.	ponen	ts qualifi	ed to this de	tail speci	fication is	s available

© BSI 02-2000 3

	[Repeat only clause numbers used, with text.		Value		
Paragraph CECC 50014	Additional values, if any, shall be given at the appropriate place without clause number(s) Curves should preferably be given in 9 of this specification.]	Symbol	min.	max.	Unit
4.4	Power dissipation Special requirements for ventilation/mounting shall be specified				
4.4.1	Maximum power dissipation under specified conditions (T_{amb} or $T_{case} = 25$ °C) and according to temperature derating curves or:	$\mathrm{P_{tot}}$		X	W
4.4.2	Maximum virtual junction temperature and absolute limit of power dissipation	$egin{array}{c} \mathbf{T_{(vj)}} \ \mathbf{P_{tot}} \end{array}$		X X	°C W
4.5	Maximum value of non repetitive on-state surge current	I_{TSM}		x	A
4.6	Maximum value of peak repetitive on-state current	${ m I}_{ m TRM}$		x	A
4.7	Maximum value of rate of change of off-state voltage	(dV) (dt)crit	·	X	kV/μs
4.8	Maximum value of peak repetitive reverse voltage (standards.if	v _{rrm} eh.ai)	IL W	X	V

5 Electrical characteristics

cs SIST See [8] of this specification for inspection https://standards.iteh.ai/catalogrequirements (Groups Al and C) del-

In the following table, characteristics marked "X" in the "value" column shall be given; characteristics marked "+" in the "measured" column are measured in Group A or Sub-Group C2.

[Signs between brackets correspond to characteristics given as "where appropriate" or as alternatives:

- Those characteristics marked "where appropriate" in this clause <u>and</u> in the inspection section shall either be omitted or, if specified, shall then be measured.
- For equivalent characteristics given as alternatives, the choice should preferably be left open to allow the use of the same detail specification by different manufacturers or countries.

Repeat only clause numbers used, with text. Any additional characteristics shall be given at the appropriate place without clause numbers.

When several devices are included in the same detail specification, the relevant values should be given on successive lines, not repeating identical values.]

Paragraph CECC Measured		Characteristics and conditions at T_{amb} or $T_{case} = 25$ °C,	G1-1	Value		TT 1.
50014	Measured	unless otherwise stated	Symbol	min.	max.	Unit
5.1	+	Minimum and maximum value of forward breakdown voltage at a specified breakdown current (I_Z)	V_{FZ}	X	X	V
5.2	+	Minimum value of reverse breakdown voltage at a specified current	V_{R}	X		V
5.3	+	Maximum value of breakover voltage	$V_{(BO)}$		X	$ \mathbf{v} $
5.3.1	+	Maximum value of dynamic breakover voltage at a specified voltage rate	$V_{(BO)dyn}$		X	V
5.4	+	Maximum value of on-state voltage at a specified pulse	$V_{ m T}$		X	V
5.5	+	Maximum and minimum value of breakover current	$I_{(BO)}$	X	X	mA
5.6	+	Minimum value of holding current at a specific condition, as specified in detail specification	$I_{\mathbf{H}}$	X		mA
5.7	+	Maximum value of off-state current at a specified voltage (V_D) ARD $PREVE$	I_D	:	X	μ A
5.8	(+)	Maximum value of turn-on-time at a specified voltage	ton		(X)	ns
5.9	(+)	Maximum value of diode capacitance at a specified voltage rate N 150014:2002	C_{tot}		(X)	pF
5.10	(+) https	When virtual junction temperature is quoted as a rating: maximum value of thermal resistance junction to ambient	Rbdc0- R _{thja}		(X)	°C/W
5.11	(+)	Maximum value of forward breakdown voltage temperature coefficient	$rac{\mathrm{dV_{FZ}}}{\mathrm{dTj}}$		(X)	%/°C
5.12	(+)	Maximum value of holding current temperature coefficient	$rac{\mathrm{dI_H}}{\mathrm{dTj}}$		(X)	%/°C

6 Marking

[Any particular information other than given in box [7] on page 3 and/or 2.5.6 of CECC 50000 shall be specified here.]

7 Ordering information

The following minimum information is necessary to order a specific device, unless otherwise specified:

- precise type number;
- CECC reference of detail specification with issue number and/or date when relevant;
- level of quality assessment as specified in Annexe IIA of CECC 50000, and, if required, screening sequence as defined in Annex VI of CECC 50000;
- any other particulars.

8 Test conditions and inspection requirements

These are given in the following tables, where the values and exact test conditions to be used should be specified as required for a given type, and as required by the relevant test in CECC 50000.

"X" shows that a value is to be inserted in the detail specification.

[When several devices are included in the same detail specification, the relevant conditions and/or values should be given on successive lines, where possible, avoiding repetition of identical conditions and/or values.

The choice between alternative tests should preferably be left open, unless very sound technical reasons forbid this. Although such tests are not strictly equivalent, they are meant to achieve the same results which are to assess the correct manufacture of a device. Alternatives are provided to take into account different equipments or methods of measurements used in various countries.]

In this section, reference to clause numbers are made with respect to CECC 50000, unless otherwise stated.

[For sampling requirements either refer to, or reproduce, values of Annex IIA of CECC 50000 (according to applicable level(s) of quality assessment in box on page 3).]

GROUP A — Lot by lot

	Conditions at T _{amb} or T _{case} = 25 °C unless otherwise stated	Inspection					
Examination or test (Ref. 4.3.4/)							
		min.	max.	Unit	Assessment		
SUB-GROUP A1					θ		
Visual inspection	4.2.1				reproduce, g to d in		
SUB-GROUP A2a					ii s ii		
Non operative devices	$I_{\rm D} > 100 \times I_{\rm D}$ max. in A2b <u>or</u>	'REV	xEW	μ A	r rej		
	$V_T > 10 \times V_T$ max, in A2b	h ai)	X	V	to, or cordin t state		
SUB-GROUP A2b	(Startate asite)	11001)			nt to		
Diode current (T-103)	V _D specified SIST EN 150014:200	2	X	μ A	ither refer to, or re 50000 (according assessment stated		
${ m I_D}$		-)64b0f-c8d	4-4809-bc	c0-	ler 000 ses		
Forward break-down (D-021) voltage ${ m V_{FZ}}$	I _D specified _{25fa587a3039/sist-en-15001}	X 2002	X	V			
Breakover voltage	As specified (see B.1 to		X	v			
$ m V_{(BO)}$	this specification)				1.21 7.94		
Breakover current	As specified (see B.2 to	X	X	mA	equ: : IIA (s) o (3)]		
$I_{(BO)}$	this specification)				g re nex rel(
Holding current I_H	As specified (see B.3 to this specification)		X	mA	[For sampling requivalues of Annex [IA applicable level(s) o box [8] on page 3)]		
On-state voltage V_T	As specified (see B.4 of		X	v	san es o icab [8] c		
	this specification)				[For sa values applica box [8]		
3.000			L	L			

NOTE The relevant min. and max. limits of Group A are referred to later on, in Groups B and C, as LSL and USL (Lower and Upper Specification Limit).

GROUP B — Lot by lot

Only tests marked "D" are destructive (see 3.5.6 of CECC 50000)

 $\begin{array}{l} LSL = Lower \; Specification \; Limit \\ USL = Upper \; Specification \; Limit \end{array} \right\} \; from \; Group \; A$

	_		Inspection				
Examination or test and reference	Conditions at T_{amb} or $T_{case} = 25~^{\circ}\mathrm{C}$ unless otherwise stated	Limits			A		
	,		max.	Unit	Assessment		
SUB-GROUP B1			•				
Dimensions (4.2.2)	4.2.2/Annex III	4.2.2 box ['	or see 7]		of oox [8]		
SUB-GROUP B3					IA o		
Lead bending (D) (4.4.9)	Force = [see 4.4.9 Test Ub]	No da	No damage		nnex I		
SUB-GROUP B4					f Ar t st		
Solderability (4.4.7)	As specified; solder bath preferred	Good	wettii	ıg	nen		
SUB-GROUP B5	[Applied in C5 instead of B5, depending on				alue		
Change of temperature (4.4.4)	assessment level] As specified (Note 1) Test-Na, Nb or Nc D PREVIEW				duce, v lity ass		
followed by either: For non-cavity devices: — accelerated damp heat (D) (4.4.2)	(standards.iteh.ai) Method I SIST EN 150014:2002				to, or reproduce, values of Annex IIA el(s) of quality assessment stated in k		
or for cavity devices (only) and Sealing (4.4.10)	iteh.ai/catalog/standards/sist/6f064b0f-c8d4-4809-bdc Test QEaQe oriQlen-150014-2002	:0-		đ.	refer ole lev		
Final measurements:					her		
$egin{array}{c} I_{ m D} \ V_{ m FZ} \end{array}$	As for A2b As for A2b	LSL	USL USL		nts eit to appl		
SUB-GROUP B8					ng		
Electrical endurance	168 h at T_{amb} max. and $V_D = V_D$ specified for I_D As specified (see Annex C of this specification)				For sampling requirements either refer to, or reproduce, values of Annex IIA of CECC 50000 (according to applicable level(s) of quality assessment stated in box [8] on page 3)]		
Final measurements:			2x		ampl 500 (e 3)]		
$ I_{\mathrm{D}} $	As for A2b		USL	μ A	For san CECC 5 on page		
$V_{ m FZ}$	As for A2b	LSL	USL	V	(FC CE on		
SUB-GROUP CTR	Attributes information for B3, B4 and B8						